



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Yamazaki, et al. Art Unit : 2815
Serial No.: 09/736,724 Examiner : Paul E. Brock
Filed : December 13, 2000
Title : INSULATED GATE SEMICONDUCTOR DEVICE AND METHOD OF
MANUFACTURING THE SAME

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Commissioner for Patents
Washington, D.C. 20231

RESPONSE

In response to the action mailed April 26, 2002, please
amend the application as follows:

In the claims:

Please amend claims 1, 7, 9, 15, 20, and 23 as follows:

SUB 7- 1. (Amended) A method of manufacturing an insulated gate
DI semiconductor device, said method comprising:

C1 forming a resist over a crystal semiconductor comprising a
part to become a channel forming region;

forming a dotted hole in said resist by patterning said
resist using electron drawing method or FIB method;

forming an intrinsic or substantially intrinsic region and
an impurity region in said part to become the channel forming

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